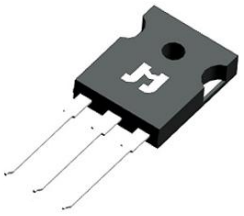
JJMICROELECTRONICS

650V 75A Trench and Field Stop IGBT

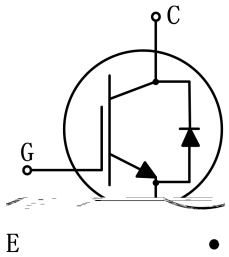
JJT75N65UK

- V_{CE} =650V
- I_C=75A@T_C=100
- $V_{CE(sat)}$=1.7V

TO-247i



- Trench and field-stop technology.
- Easy parallel switching capability.



- High efficiency for inverters.
- High ruggedness performance.
- RoHS compliant.

- PFC applications
- Uninterruptible power supplies
- Solar inverters

Type	Marking	Package	Packaging Method
JJT75N65UK	T7565UK	TO-247i（内绝缘）	Tube

V_{CES}	Collector-emitter voltage	650	V
V_{GES}	Gate-emitter voltage	±20	V
	Transient gate-emitter voltage($t_p \leq 10\mu s$, $D<0.010$)	±30	V
I_C	Continuous collector current (T_C=25)	150	A
	Continuous collector current (T_C=100)	75	A
I_{CM}	Pulsed collector current, t_p limited by T_{vjmax}	300	A
I_F	Diode continuous forward current (T_C=100)	75	A
I_{FM}	Diode maximum current, t_p limited by T_{vjmax}	300	A
P_{tot}	Power dissipation (T_C=25)	535	W
	Power dissipation (T_C=100)	267	W
T_{vj}	Operating junction temperature range	-40 to +175	
T_{stg}	Storage temperature range	-55 to +175	

$R_{th(j-c)}$	Thermal resistance, junction to case for IGBT	-	0.35	K/ W
$R_{th(j-c)}$	Thermal resistance, jun			

(T_{vj}=25℃ unless otherwise specified)

Static characteristics

BV_{CES}	Collector-emitter breakdown voltage	V_{GE}=0V, I_C=250μA	650	-	-	V
I_{CES}	Collector-emitter leakage current	V_{CE}=650V, V_{GE}=0V	-	-	50	μA
I_{GES}	Gate leakage current, forward	V_{GE}=20V, V_{CE}=0V	-	-	100	nA
	Gate leakage current, reverse	V_{GE}=-20V, V_{CE}=0V	-	-	-100	nA
$V_{GE(th)}$	Gate-emitter threshold voltage	V_{GE}=V_{CE}, I_C=1mA	4.7	5.2	5.7	V
$V_{CE(sat)}$	Collector-emitter saturation voltage	V_{GE}=15 V, I_C=75A	1.60	1.72	1.90	V
		V_{GE}=15V, I_C=75A, T_{vj} =175	-	2.3	-	V

Dynamic characteristics

C_{ies}	Input capacitance	V_{CE}=30V V_{GE}=0V f=1MHz	-	4290	-	pF
C_{oes}	Output capacitance		-	195	-	pF
C_{res}	Reverse transfer capacitance		-	20	-	pF
Q_g	Total gate charge	V_{CC}=520V V_{GE}=15V I_C=75A	-	130	-	nC

(T_{vj}=25℃ unless otherwise specified)

V_F	Diode forward voltage	I_F=75A	0.95	1.1	1.25	V
		I_F=75A,T_{vj}=175℃	-	0.95	-	V
t_{rr}	Diode reverse recovery time	V_R=400V I_F=75A di_F/dt=-450A/ s	-	610	-	ns
I_{rrm}	Diode peak reverse recovery current		-	15	-	A
Q_{rr}	Diode reverse recovery charge		-	4950	-	nC
t_{rr}	Diode reverse recovery time	V_R=400V I_F=75A di_F/dt=-450A/ s T_{vj}=175℃	-	745	-	ns
I_{rrm}	Diode peak reverse recovery current		-	24	-	A
Q_{rr}	Diode reverse recovery charge		-	14500	-	nC

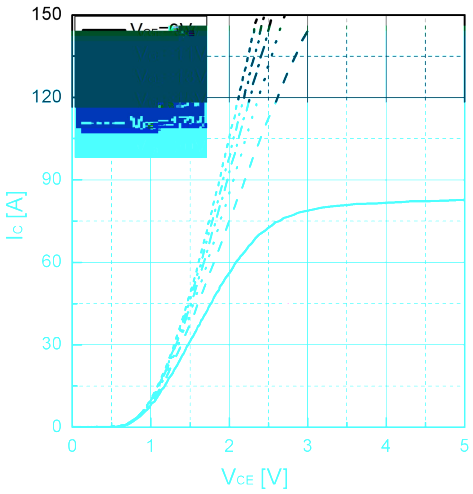


Fig 1. Typical output characteristic (T_{vj}=25℃)

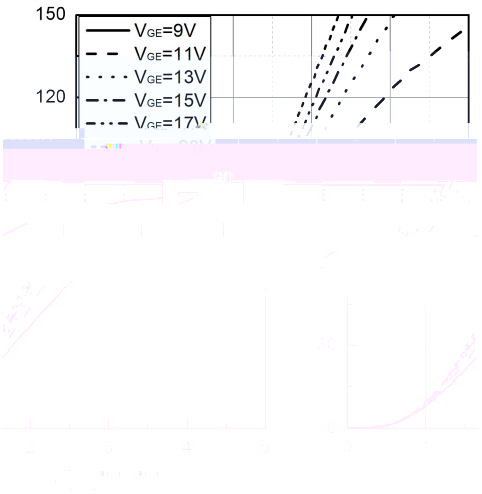


Fig 2. Typical output characteristic(T_{vj}=175℃)

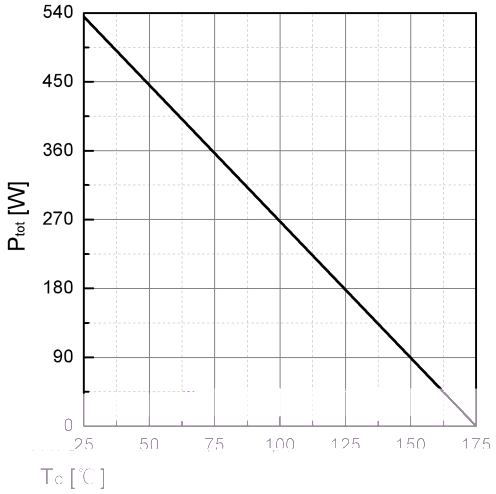


Fig 3. Power dissipation as a function of T_C

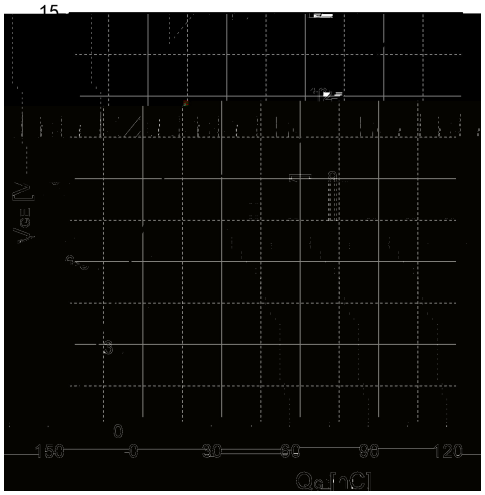


Fig 4. Typical Gate charge

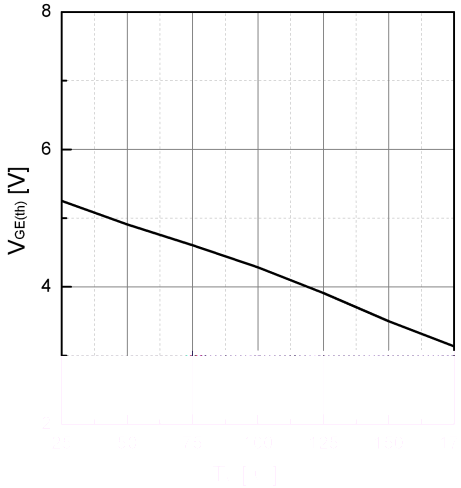


Fig 5. Typical $V_{GE(th)}$ as a function of T_{vj} (I_C=1mA)

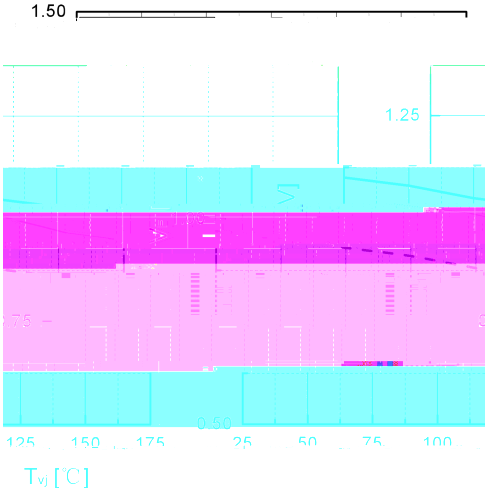


Fig 6. Typical V_F as a function of T_{vj}

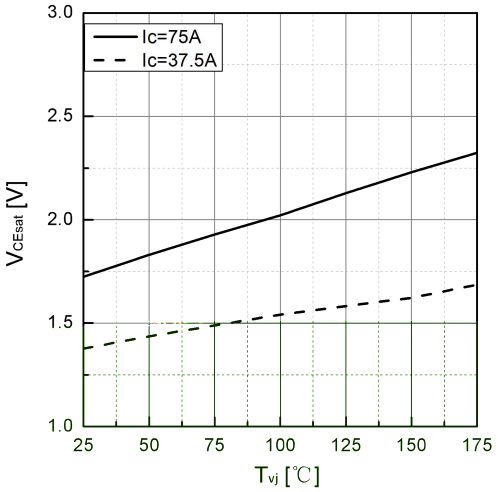


Fig 7. Typical V_{CEsat} as a function of T_{vj}

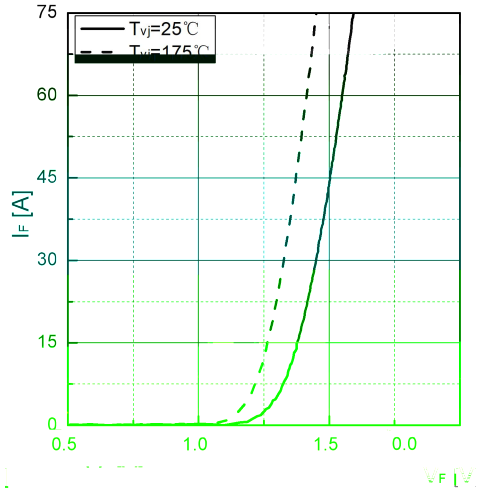


Fig 8. Typical I_F as a function of V_F

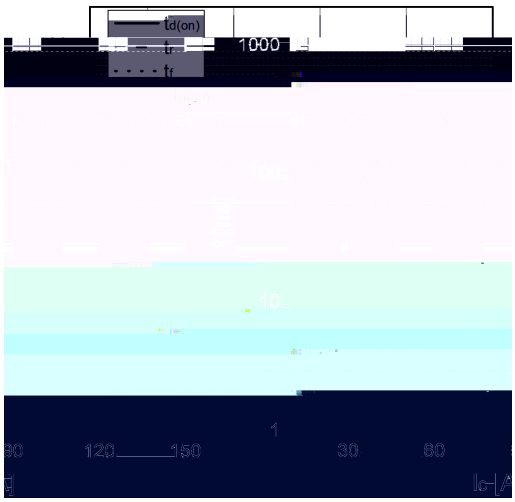


Fig 9. Typical switching time as a function of I_C

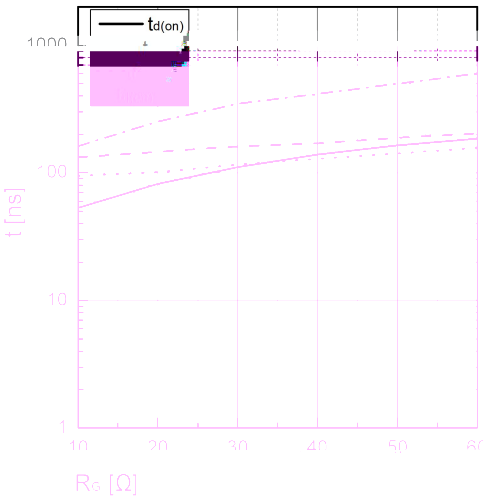


Fig 10. Typical switching times as a function of R_G

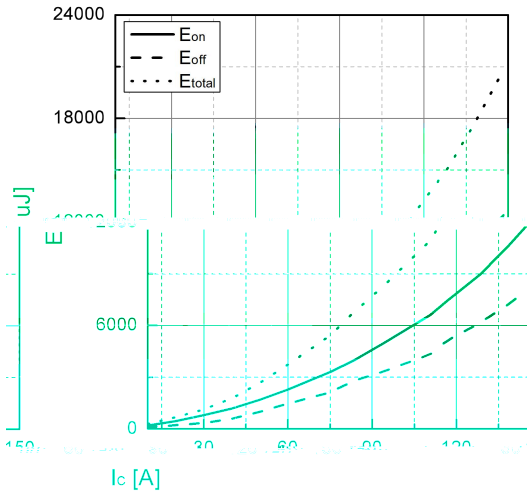


Fig 11. Typical switching energy losses as a function of I_C

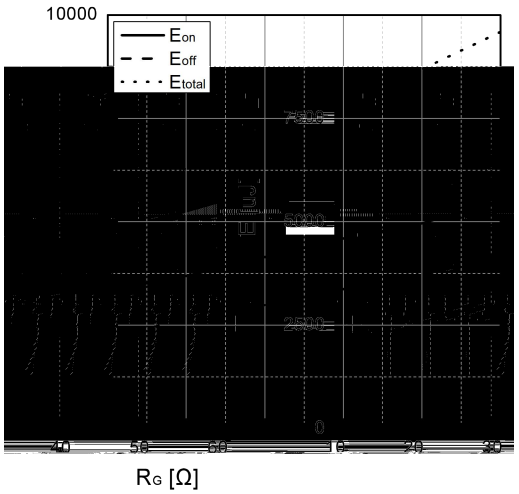


Fig 12. Typical switching energy losses as a function of R_G

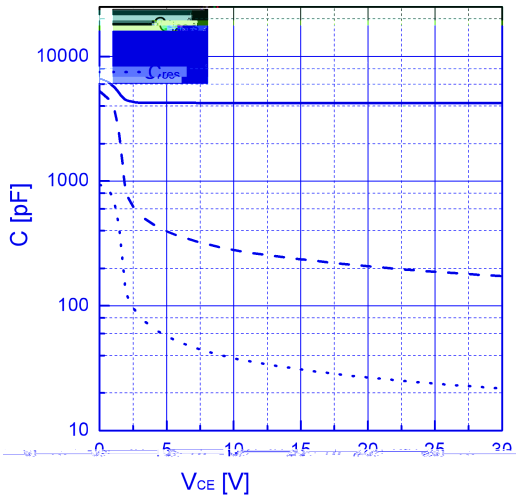


Fig 13. Typical capacitance as a function of V_{CE} (f=1Mhz, V_{GE}=0V)

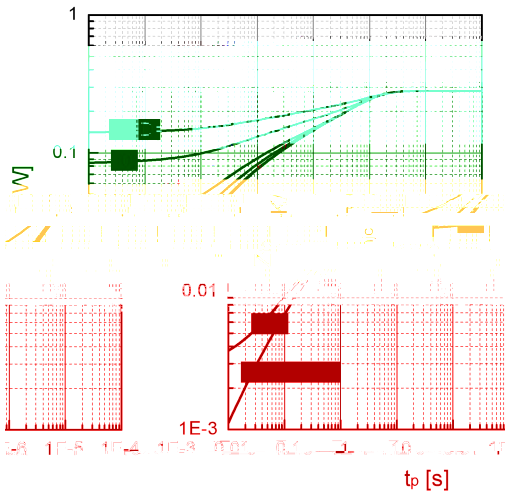
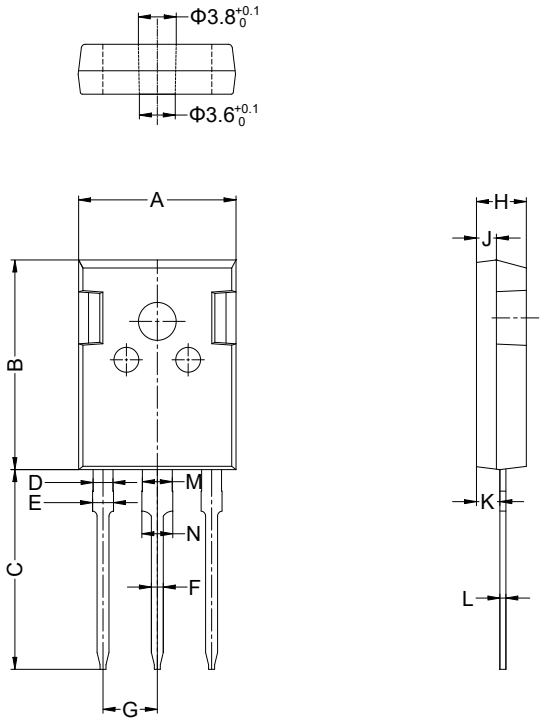


Fig 14. Transient thermal impedance of IGBT

TO-247



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.50	15.80	16.10	0.610	0.622	0.634
B	20.80	21.00	21.20	0.819	0.827	0.835
C	19.70	20.00	20.30	0.776	0.787	0.799
D	1.80	2.00	2.20	0.071	0.079	0.087
E	1.90	2.10	2.30	0.075	0.083	0.091
F	1.00	1.20	1.40	0.039	0.047	0.055
G	5.25	-	5.65	0.207	-	0.222
H	4.80	5.00	5.20	0.189	0.197	0.205
J	1.90	2.00	2.10	0.075	0.079	0.083
K	2.20	2.35	2.50	0.087	0.093	0.098
L	0.41	0.60	0.79	0.016	0.024	0.031
M	2.80	3.00	3.20	0.110	0.118	0.126
N	2.90	3.10	3.30	0.114	0.122	0.130

Date	Revision	Changes
2025-7-8	Rev 1.0	Release of the Datasheet
2025-9-5	Rev 1.1	